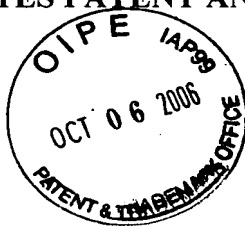


TfW/2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Masanobu ANDO, et al.



Serial No.: 10/564,416

Group Art Unit: 2811

Filing Date: January 12, 2006

Examiner: Sara W. Crane

For: LIGHT EMITTING SEMICONDUCTOR DEVICE AND A METHOD OF
MANUFACTURING IT

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

Submission of European Office Action

Sir:

Applicants submit the European Search Report dated June 2, 2006, in a counterpart foreign application and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. The European Office Action refers to references previously made of record in the present case.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,

Date: 10/6/06

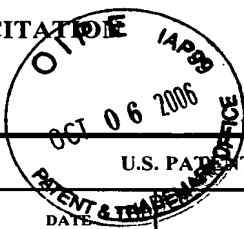
**McGinn Intellectual Property
Law Group, PLLC**

8321 Old Courthouse Road, Suite 200
Vienna, Virginia 22182-3817
(703) 761-4100
Customer No. 21254

John W. Fitzpatrick, Esq.
Registration No.: 41,018

Sean M. McGinn, Esq.
Registration No.: 34,386

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)



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| Docket Number (Optional) F05-420-US | Application Number 10/564,416 |
| Applicant(s) Masanobu ANDO, et al. | |
| Filing Date January 12, 2006 | Group Art Unit 2811 |

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

| REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation | |
|-----|-------------------------|-----------------------|-------------------|--|----------|-------------|----|
| | | | | | | YES | NO |
| | EP-0-662 739 | 07/12/1995 | Europe | Previously submitted with IDS dated 4/12/06 | | | |
| | 11-026812 | 01/29/1999 | Japan | Previously submitted with IDS dated 4/12/06 | | | |
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

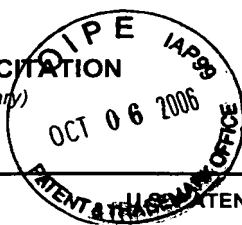
| | |
|--|---|
| | European Search Report dated June 2, 2006 |
| | Kneissl, Michael, et al., "Continuous-wave ultraviolet InGaN/InAlGaN multiple quantum well laser diodes", Applied Physic Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, 012033738 Previously submitted with IDS dated 4/12/06 |

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.

F05-420-US

APPLICATION NO.

10/564,416

APPLICANT(S)

Masanobu ANDO, et al.

FILING DATE

January 12, 2006

GROUP ART UNIT

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| | | <p>Nakamura, et al., "InGaN/GaN/AlGaIn-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, US, Vol. 72, No. 2, January 12, 1998</p> <p>previously submitted with IDS dated 4/12/08</p> |
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EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.